

ABSTRACT

A resist composition and a method of forming a resist pattern that enable contamination within the exposure apparatus to be prevented in lithography processes using an electron beam or EUV (extreme ultraviolet light). In this method, an organic solvent containing, as the principal component, one or more compounds selected from a group consisting of propylene glycol monomethyl ether (PGME), methyl amyl ketone (MAK), butyl acetate (BuOAc), and 3-methyl methoxy propionate (MMP) is used as the resist solvent.